

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	9591	(@ad<"20010612") and gate and (semiconductor or "ic" or chip or die) and (locos or ((dielectric or insulation) near (trench or gap or recess or via)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/02 13:43
L2	5214	(@ad<"20010612") and 438/196, 207,218,219,248,294,295,296, 318,353,355,359,391,404,439, 362,297,225.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/02 13:44
L3	3017	L2 and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/02 14:03
L4	785	L2 and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/02 14:04
L5	591	L4 and ((etch or etching) with (oxide or insulation or dielectric))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/02 14:06
L6	32	L4 and (((etch or etching) and cleaning) with (oxide or insulation or dielectric))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/02 14:48
L7	22	L4 and (((first and second) near (etch or etching)) with (oxide or insulation or dielectric))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/02 14:49